

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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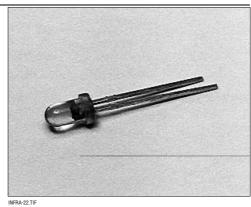




Silicon Phototransistor

FEATURES

- T-1 plastic package
- 20° (nominal) acceptance angle
- · Consistent optical properties
- · Wide sensitivity ranges
- Mechanically and spectrally matched to SEP8505 and SEP8705 infrared emitting diodes

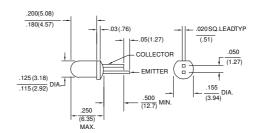


DESCRIPTION

The SDP8405 is an NPN silicon phototransistor transfer molded in a T-1 clear plastic package. Transfer molding of this device assures superior optical centerline performance compared to other molding processes. Lead lengths are staggered to provide a simple method of polarity identification.

OUTLINE DIMENSIONS in inches (mm)

3 plc decimals ±0.005(0.12) 2 plc decimals ±0.020(0.51)



DIM_100.ds4



Silicon Phototransistor

ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Light Current	l _L				mA	V _{CE} =5 V
SDP8405-001		1.00				H=5 mW/cm ^{2 (1)}
SDP8405-002		7.00		14.0		
SDP8405-003		12.0		24.0		
Light Current	I∟				mA	V _{CE} =5 V
SDP8405-011		0.16				H=0.25 mW/cm ^{2 (2)}
SDP8405-012		0.16		0.46		
SDP8405-013		0.32		0.92		
SDP8405-014		0.64		1.85		
SDP8405-015		1.25				
Collector Dark Current	ICEO			100	nA	V _{CE} =15 V, H=0
Collector-Emitter Breakdown Voltage	V _(BR) ceo	30			V	Ic=100 μA
Emitter-Collector Breakdown Voltage	V _{(BR)ECO}	5.0			V	I _E =100 μA
Collector-Emitter Saturation Voltage	Vce(sat)			0.4	V	lc=l∟/8
SDP8405-001 to -003						H=5 mW/cm ²
SDP8405-011 to -015						H=0.25 mW/cm ²
Angular Response (3)	Ø		20		degr.	I _F =Constant
Rise And Fall Time	t _r , t _f		15		μs	Vcc=5 V, I _L =1 mA
						R _L =1000 Ω

- Notes
 1. The radiation source is a tungsten lamp operating at a color temperature of 2870°K.
 2. The radiation source is an IRED with a peak wavelength of 935 nm.
 3. Angular response is defined as the total included angle between the half sensitivity points.

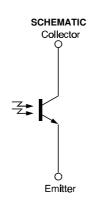
ABSOLUTE MAXIMUM RATINGS

(25°C Free-Air Temperature unless otherwise noted) Collector-Emitter Voltage 30 V 5 V Emitter-Collector Voltage Power Dissipation 70 mW (1) Operating Temperature Range -40°C to 85°C Storage Temperature Range -40°C to 85°C Soldering Temperature (5 sec) 240°C

Notes

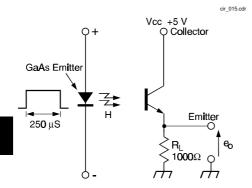
1. Derate linearly from 25°C free-air temperature at the rate of

0.18 mW/°C.



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SWITCHING TIME TEST CIRCUIT



SWITCHING WAVEFORM

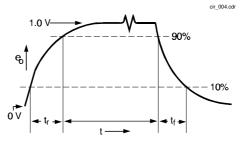


Fig. 1 Responsivity vs Angular Displacement

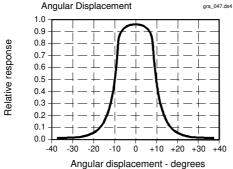


Fig. 2 Collector Current vs

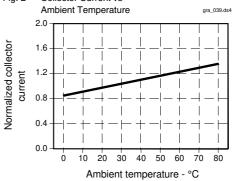


Fig. 3 Dark Current vs

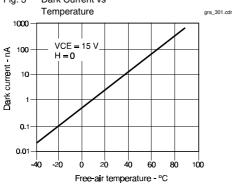
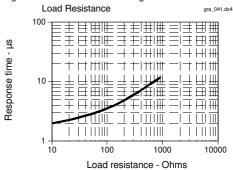


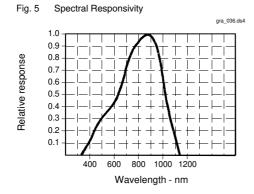
Fig. 4 Non-Saturated Switching Time vs

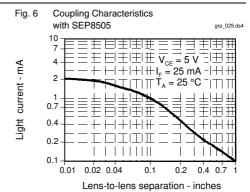


Honeywell

Honeywell reserves the right to make changes in order to improve design and supply the best products possible.

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All Performance Curves Show Typical Values